

DATA SHEET

Triacs and Diacs

Order code	Manufacturer code	Description
47-3412	DB3	DB3 32V DIAC DO-35 (ST)

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The enclosed information is believed to be correct, Information may change 'without notice' due to	Revision A
product improvement. Users should ensure that the product is suitable for their use. E. & O. E.	04/07/2003

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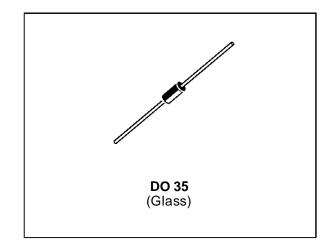


DB3 /DB4 / DC34

TRIGGER DIODES

FEATURES

- V_{BO}: 32V/34V/40V VERSIONS
- LOW BREAKOVER CURRENT



DESCRIPTION

High reliability glass passivation insuring parameter stability and protection against junction contamination.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit	
Р	Power dissipation on printed circuit (L = 10 mm)	Ta = 65 °C	150	mW
I _{TRM}	Repetitive peak on-state current	tp = 20 μs F= 100 Hz	2	А
Tstg Tj	Storage and operating junction temperat	ure range	- 40 to + 125 - 40 to + 125	ပို့

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th (j-a)}	Junction to ambient	400	°C/W
R _{th (j-l)}	Junction-leads	150	°C/W

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ELECTRICAL CHARACTERISTICS $(Tj = 25^{\circ}C)$

Symbol	Parameter	Test Conditions			Value		Unit
				DB3	DC34	DB4	
V _{BO}	Breakover voltage *	C = 22nF** see diagram 1	MIN	28	30	35	V
			TYP	32	34	40	
			MAX	36	38	45	
[I+V _{BO} I-I-V _{BO} I]	Breakover voltage symmetry	C = 22nF** see diagram 1	MAX		± 3		V
IΔV± I	Dynamic breakover voltage *	$\Delta I = [I_{BO} \text{ to } I_{F}=10\text{mA}]$ see diagram 1	MIN		5		V
Vo	Output voltage *	see diagram 2	MIN		5		V
I _{BO}	Breakover current *	C = 22nF **	MAX	100	50	100	μА
tr	Rise time *	see diagram 3	TYP		1.5		μs
I _B	Leakage current *	V _B = 0.5 V _{BO} max see diagram 1	MAX		10		μА

^{*} Electrical characteristic applicable in both forward and reverse directions.

DIAGRAM 1: Current-voltage characteristics

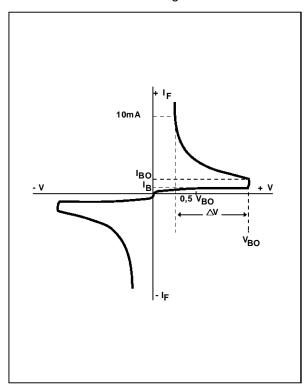


DIAGRAM 2: Test circuit for output voltage

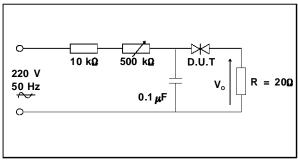
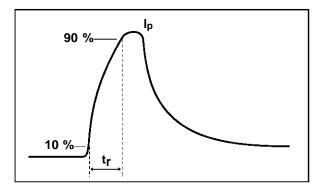


DIAGRAM 3 : Test circuit see diagram 2. Adjust R for lp=0.5A



^{**} Connected in parallel with the devices.

Fig.1: Power dissipation versus ambient temperature (maximum values)

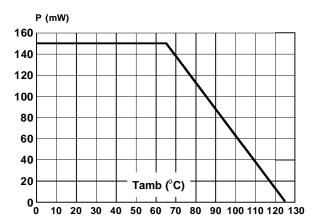


Fig.2 : Relative variation of V_{BO} versus junction temperature (typical values)

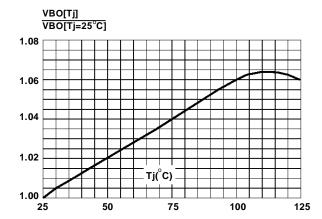
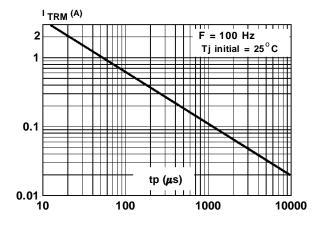
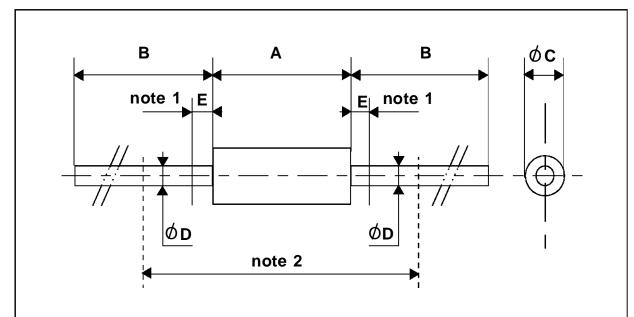


Fig.3: Peak pulse current versus pulse duration (maximum values)



PACKAGE MECHANICAL DATA (in millimeters)

DO 35 Glass



NOTES		ISIONS	DIMEN		REF.	
	Inches		Millimeters			
	Max.	Min.	Max.	Min.		
1 - The lead diameter Ø D is not controlled over zone	0.117	0.120	4.500	3.050	А	
2 - The minimum axial lengh within which the device r		0.500		12.7	В	
placed with its leads bent at right angles is 0.59"(15 m	0.079	0.060	2.000	1.530	ØC	
	0.022	0.018	0.558	0.458	Ø D	
$\vec{-}$	0.050		1.27		Е	

in which the device may be angles is 0.59"(15 mm)

Cooling method by convection and conduction

Marking: type number

Weight: 0.15 g

Polarity: NA Stud torque: NA

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